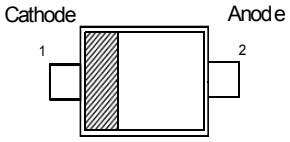
迈拓电子
MAITUO ELECTRONIC

Surface Mount Schottky Barrier Diodes

Features

• Low Forward Voltage



SOD-523

MARKING

SD103AWT:S4 **SD103BWT:S5** **SD103CWT:S6**

Absolute Maximum Ratings (T_a = 25 °C)

Parameter		Symbol	Value	Unit
Peak Repetitive Reverse Voltage	SD103AWT SD103BWT SD103CWT	V_{RRM}	40 30 20	V
Reverse Voltage	SD103AWT SD103BWT SD103CWT	V_R	40 30 20	V
Average Forward Rectified Current		$I_{F(AV)}$	350	mA
Non-Repetitive Peak Forward Surge Current at t = 1 s		I_{FSM}	2	A
Power Dissipation		P_{tot}	200	mW
Operating and Storage Temperature Range		T_j, T_{stg}	- 65 to + 125	°C

Characteristics at T_a = 25 °C

Parameter		Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at I_R=10uA	SD103AWT SD103BWT SD103CWT	$V_{(BR)R}$	40 30 20	- - -	- - -	V
Reverse Leakage Current at V_R =30V at V_R = 20 V at V_R = 10 V	 SD103AWT SD103BWT SD103CWT	I_R	 - - -	 - - -	 5 5 5	μA
Forward Voltage at I_F = 20 mA at I_F = 200 mA		V_F	 - -	 - -	 0.37 0.6	V
Total Capacitance at V_R = 0 V, f = 1 MHz		C_T	-	50	-	pF
Reverse Recovery Time at I_F = I_R = 200 mA, I_{rr} = 0.1 I_R, R_L = 100 Ω		t_{rr}	-	10	-	ns

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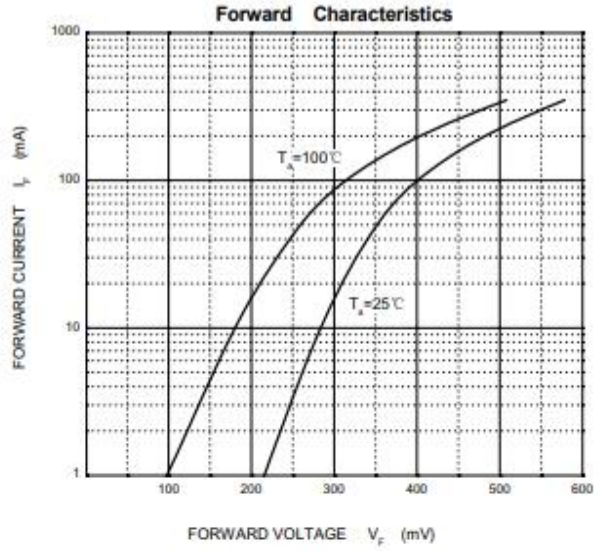
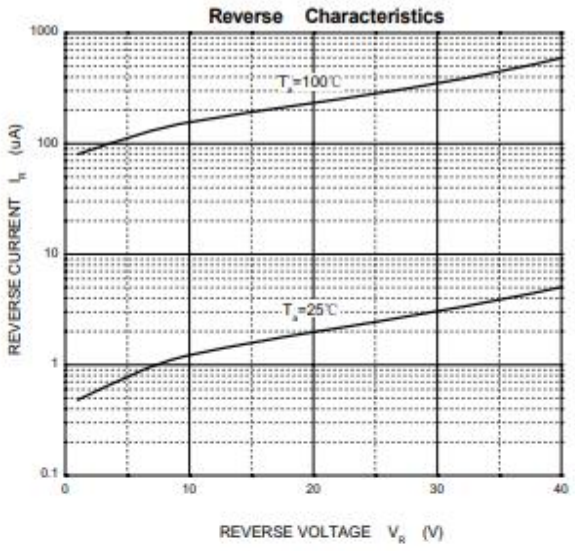
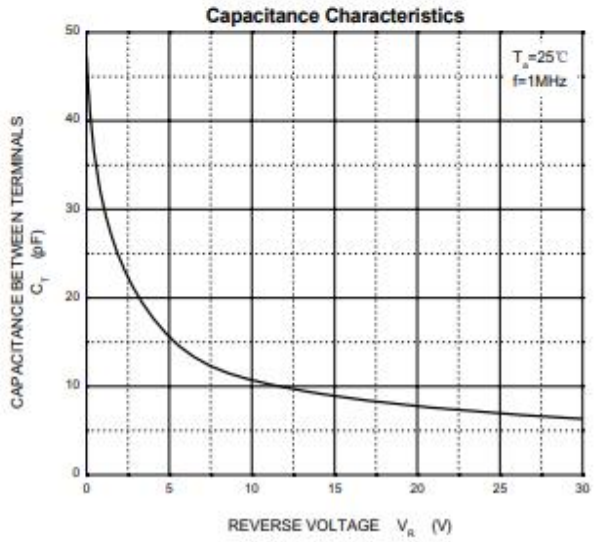
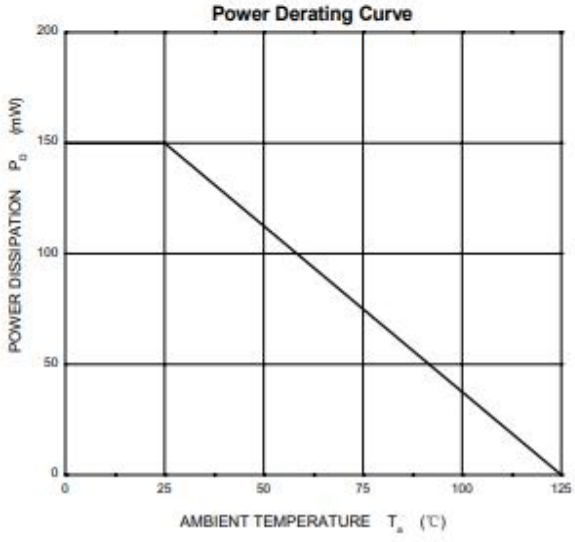
Typical Characteristics









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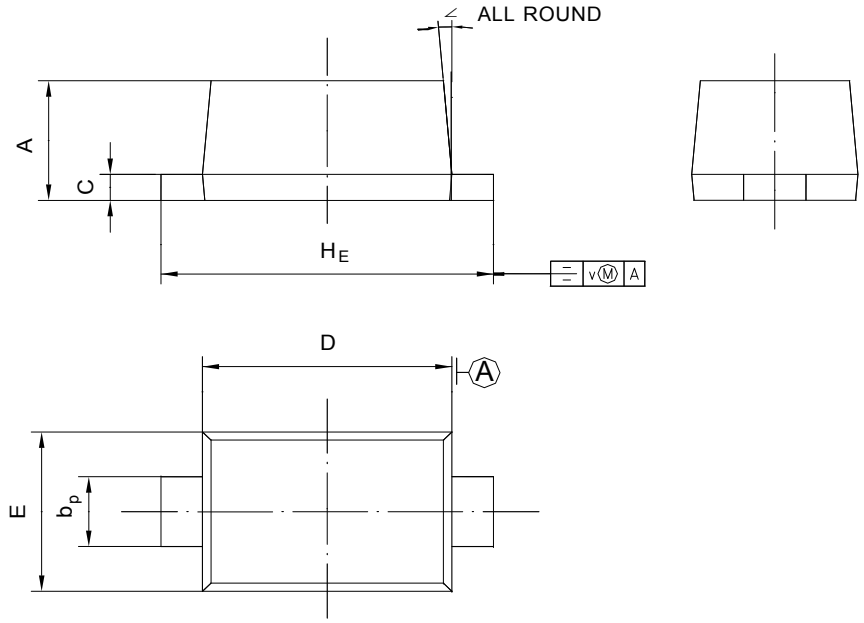
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads **SOD-523**



UNIT	A	b_p	C	D	E	H_E	V	∠
mm	0.68 0.58	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°